

**LOGIC LEVEL
HEXFET® POWER MOSFET
SURFACE MOUNT (SMD-0.5)**

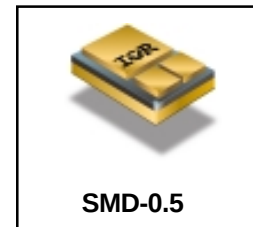
**IRL5NJ7404
20V, P-CHANNEL**

Product Summary

Part Number	BV _{DSS}	R _{DS(on)}	I _D
IRL5NJ7404	-20V	0.04Ω	-11A

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon unit area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

These devices are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits.



SMD-0.5

Features:

- Logic Level Gate Drive
- Low R_{DS(on)}
- Avalanche Energy Ratings
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Light Weight

Absolute Maximum Ratings

	Parameter		Units
I _D @ V _{GS} = -10V, T _C = 25°C	Continuous Drain Current	-11	A
I _D @ V _{GS} = -10V, T _C = 100°C	Continuous Drain Current	-7.0	
I _{DM}	Pulsed Drain Current ①	-44	
P _D @ T _C = 25°C	Max. Power Dissipation	50	W
	Linear Derating Factor	0.4	W/°C
V _{GS}	Gate-to-Source Voltage	±12	V
E _{AS}	Single Pulse Avalanche Energy ②	157	mJ
I _{AR}	Avalanche Current ①	-11	A
E _{AR}	Repetitive Avalanche Energy ①	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	0.7	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Package Mounting Surface Temperature	300 (for 5 s)	
	Weight	1.0 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔBV _{DSS} /ΔT _j	Temperature Coefficient of Breakdown Voltage	—	0.14	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.04 0.07	Ω	V _{GS} = -4.5V, I _D = -11A ④ V _{GS} = -2.7V, I _D = -7.0A
V _{GS(th)}	Gate Threshold Voltage	-0.7	—	—	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	9.0	—	—	S (r)	V _{DS} = -15V, I _{DS} = -3.2A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-1.0 -25	μA	V _{DS} = -16V, V _{GS} = 0V V _{DS} = -16V, V _{GS} = 0V, T _j = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -12V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100	nA	V _{GS} = 12V
Q _g	Total Gate Charge	—	—	50	nC	V _{GS} = -4.5V, I _D = -3.2A V _{DS} = -16V
Q _{gs}	Gate-to-Source Charge	—	—	5.5	nC	
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	21	nC	
t _{d(on)}	Turn-On Delay Time	—	—	20	ns	V _{DD} = -10V, I _D = -3.2A, V _{GS} = -4.5V, R _G = 6.0Ω
t _r	Rise Time	—	—	150		
t _{d(off)}	Turn-Off Delay Time	—	—	65		
t _f	Fall Time	—	—	90		
L _S + L _D	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	1450	—	pF	V _{GS} = 0V, V _{DS} = -15V f = 1.0MHz
C _{oss}	Output Capacitance	—	830	—		
C _{rss}	Reverse Transfer Capacitance	—	430	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-11	A	T _j = 25°C, I _S = -3.2A, V _{GS} = 0V ④ T _j = 25°C, I _F = -3.2A, di/dt ≤ 100A/μs V _{DD} ≤ -20V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	-44		
V _{SD}	Diode Forward Voltage	—	—	-1.0	V	
t _{rr}	Reverse Recovery Time	—	—	80	ns	
Q _{RR}	Reverse Recovery Charge	—	—	100	nC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	2.5	°C/W	

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

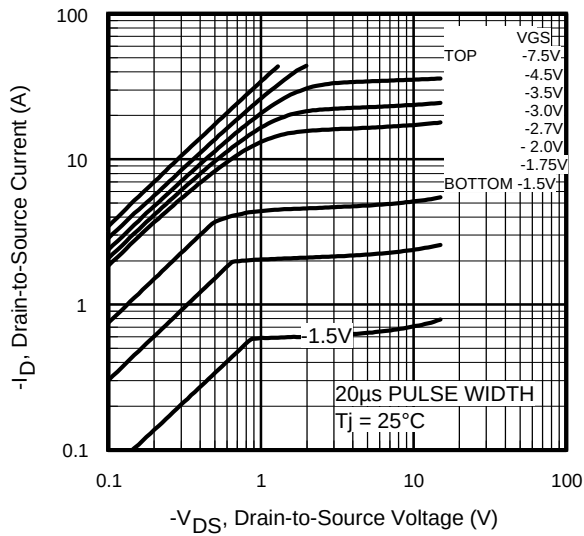


Fig 1. Typical Output Characteristics

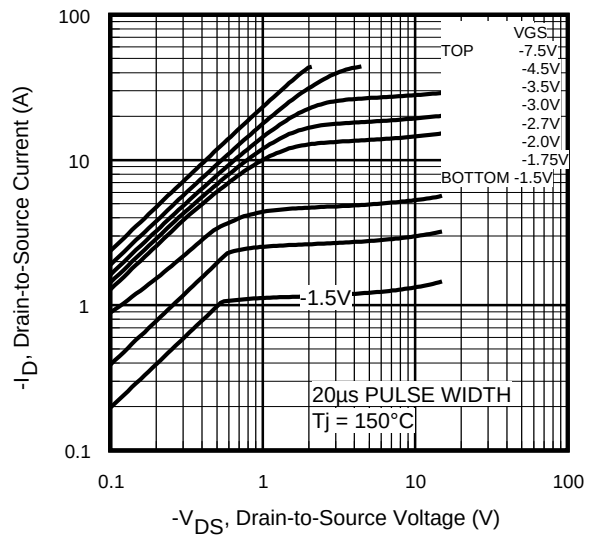


Fig 2. Typical Output Characteristics

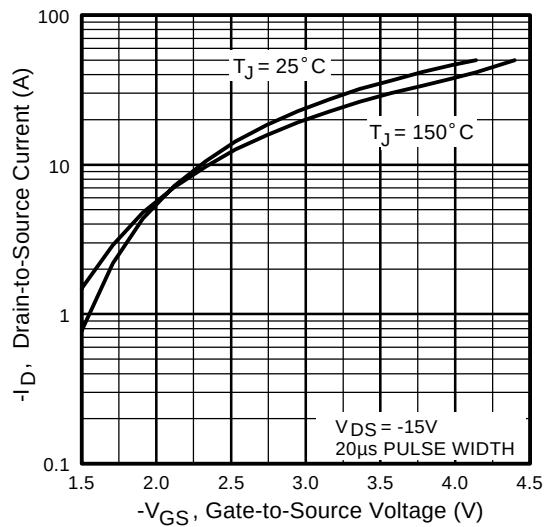


Fig 3. Typical Transfer Characteristics

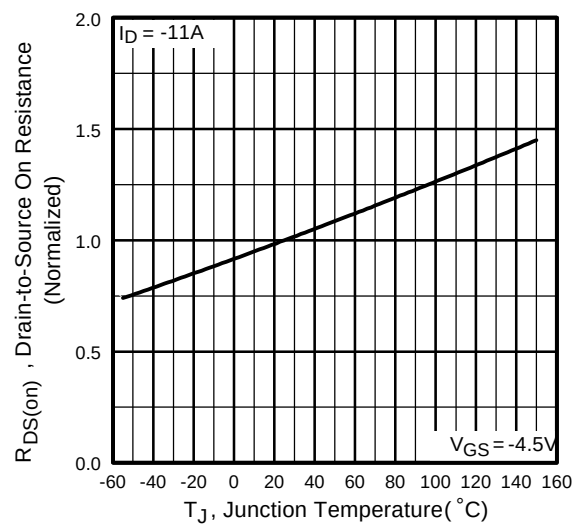
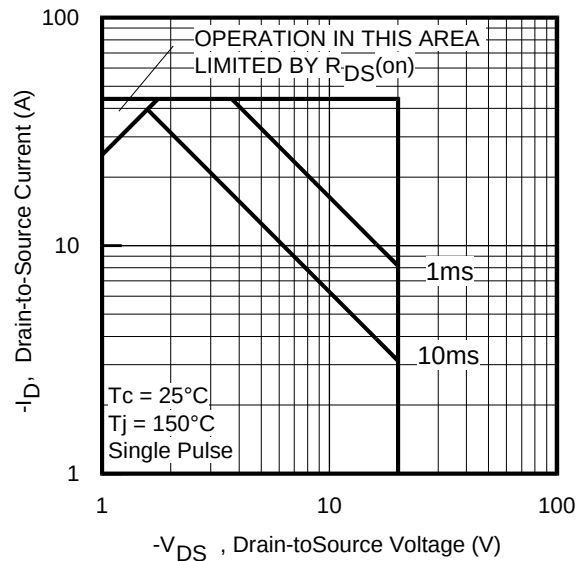
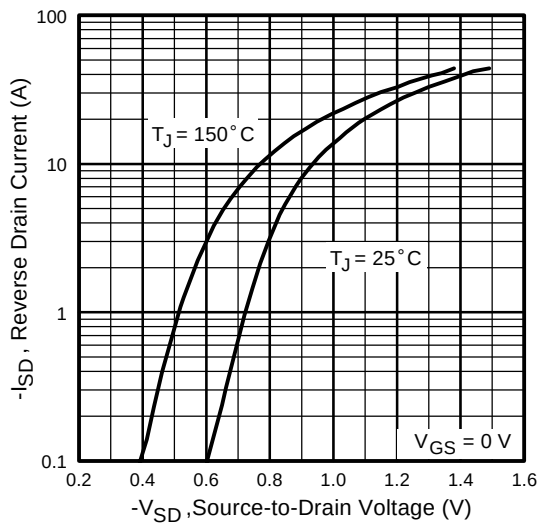
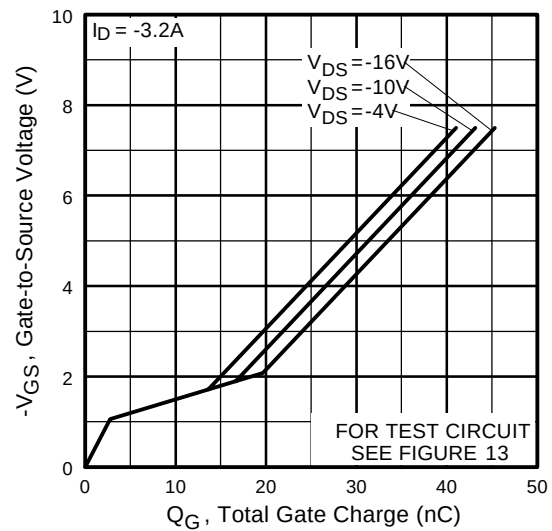
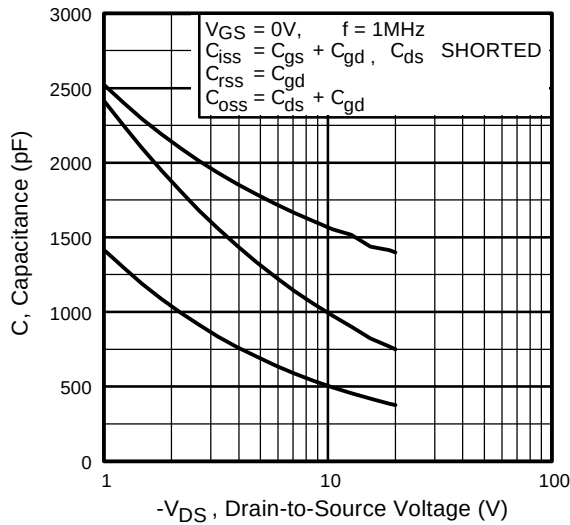


Fig 4. Normalized On-Resistance
Vs. Temperature



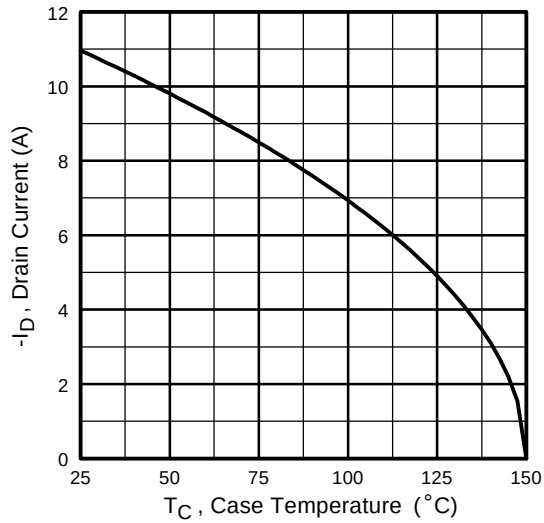


Fig 9. Maximum Drain Current Vs. Case Temperature

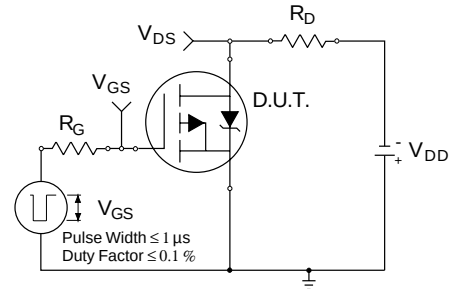


Fig 10a. Switching Time Test Circuit

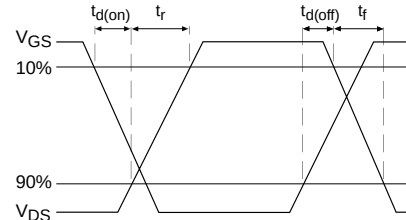


Fig 10b. Switching Time Waveforms

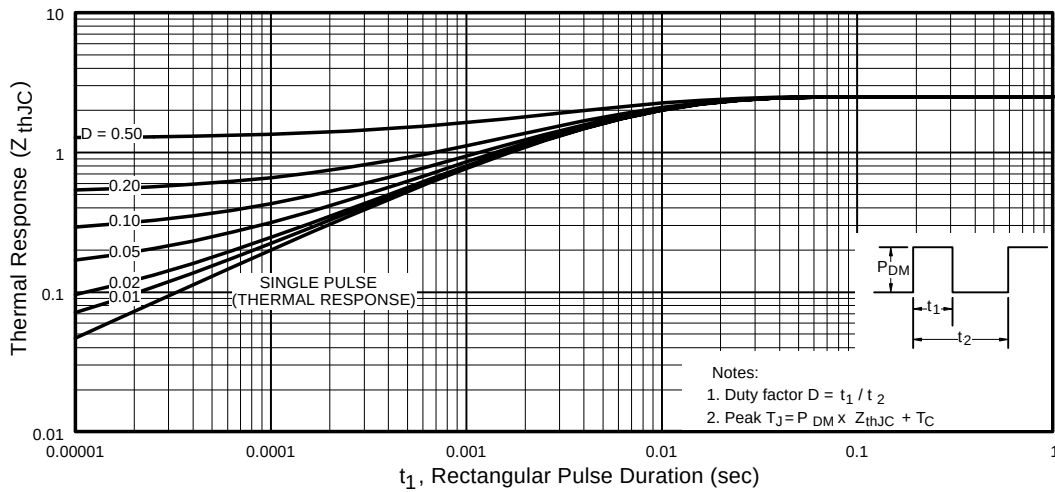


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

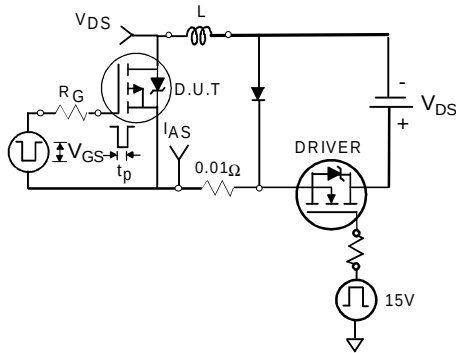


Fig 12a. Unclamped Inductive Test Circuit

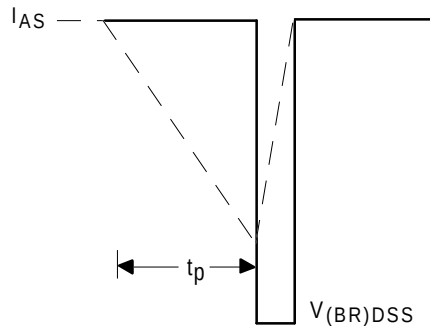


Fig 12b. Unclamped Inductive Waveforms

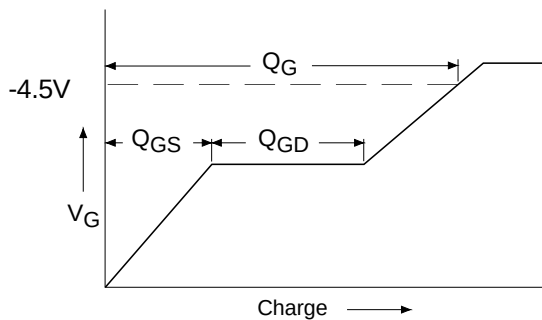


Fig 13a. Basic Gate Charge Waveform

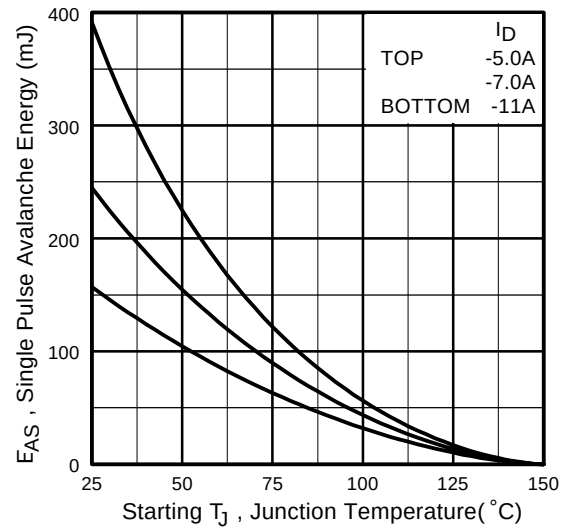


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

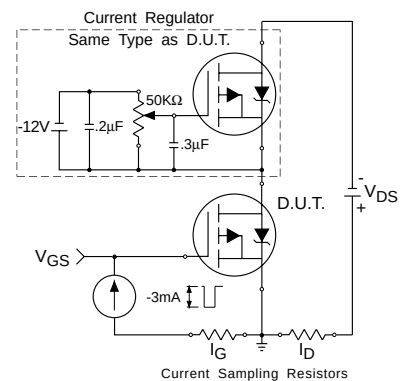
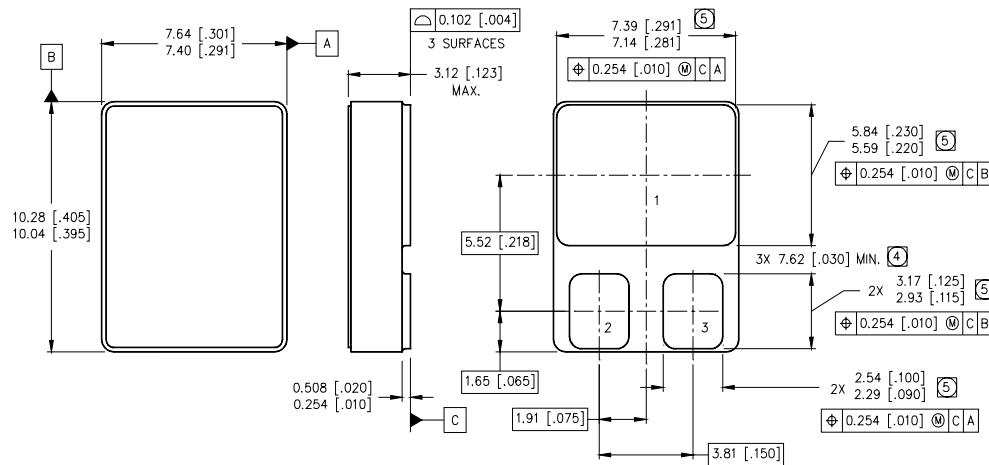


Fig 13b. Gate Charge Test Circuit

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = -15\text{ V}$, Starting $T_J = 25^\circ\text{C}$, $L = 2.6\text{ mH}$
Peak $I_{AS} = -11\text{ A}$, $V_{GS} = -10\text{ V}$, $R_G = 25\Omega$
- ③ $I_{SD} \leq -11\text{ A}$, $di/dt \leq -84\text{ A}/\mu\text{s}$,
 $V_{DD} \leq -20\text{ V}$, $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$

Case Outline and Dimensions — SMD-0.5



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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